



N-Channel 250-V (D-S) 175 °C MOSFET

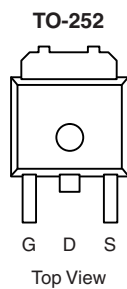
PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
250	0.165 at V _{GS} = 10 V	17

FEATURES

- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature

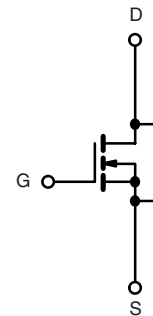


RoHS COMPLIANT



Drain Connected to Tab

Ordering Information: SUD17N25-165-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	250	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 175 °C) ^b	I _D	T _C = 25 °C	17
		T _C = 125 °C	9.8
Pulsed Drain Current	I _{DM}	20	A
Continuous Source Current (Diode Conduction)	I _S	17	
Single Pulse Avalanche Current	I _{AS}	5	
Single Pulse Avalanche Energy	E _{AS}	L = 0.1 mH 1.25	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	136 ^b
		T _A = 25 °C	3 ^a
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 sec	15	18	°C/W
		Steady State	40	50	
Junction-to-Case (Drain)	R _{thJC}	0.85	1.1		

Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. See SOA curve for voltage derating.

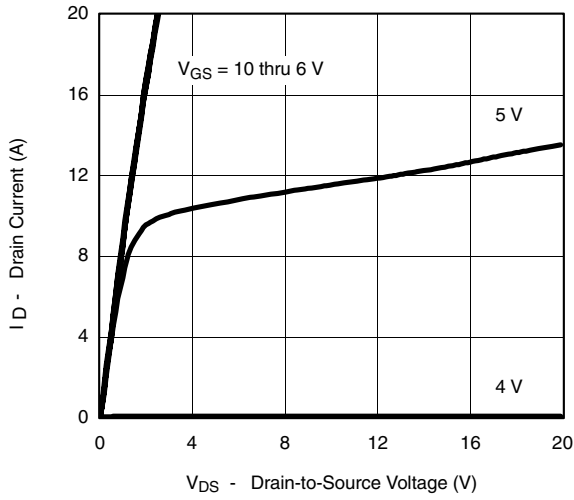
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	250			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		4.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}$	17			A
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 14\text{ A}$		0.131	0.165	Ω
		$V_{GS} = 10\text{ V}, I_D = 14\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.347	
		$V_{GS} = 10\text{ V}, I_D = 14\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.462	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 17\text{ A}$		36		S
Dynamic^a						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		1950		μF
Output Capacitance	C_{oss}			160		
Reverse Transfer Capacitance	C_{rss}			70		
Total Gate Charge ^c	Q_g	$V_{DS} = 125\text{ V}, V_{GS} = 10\text{ V}, I_D = 17\text{ A}$		30	42	nC
Gate-Source Charge ^c	Q_{gs}			10		
Gate-Drain Charge ^c	Q_{gd}			10		
Gate Resistance	R_g			1.6		Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 125\text{ V}, R_L = 7.35\text{ }\Omega$ $I_D \equiv 17\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		15	25	ns
Rise Time ^c	t_r			130	195	
Turn-Off Delay Time ^c	$t_{d(off)}$			30	45	
Fall Time ^c	t_f			100	150	
Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$)						
Pulsed Current	I_{SM}				20	A
Diode Forward Voltage ^b	V_{SD}	$I_F = 17\text{ A}, V_{GS} = 0\text{ V}$		0.9	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 17\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		115	175	ns

Notes:

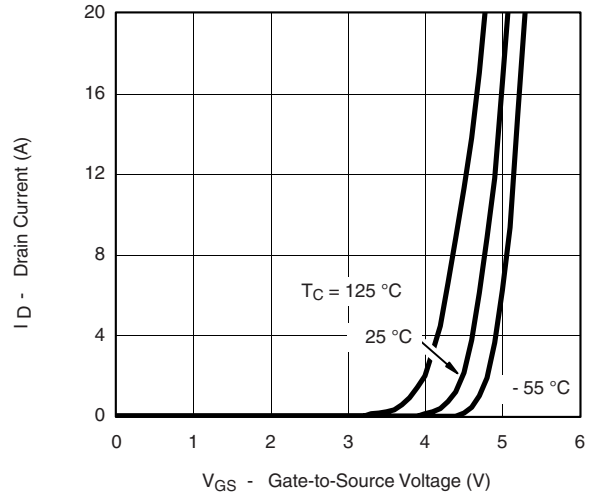
- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

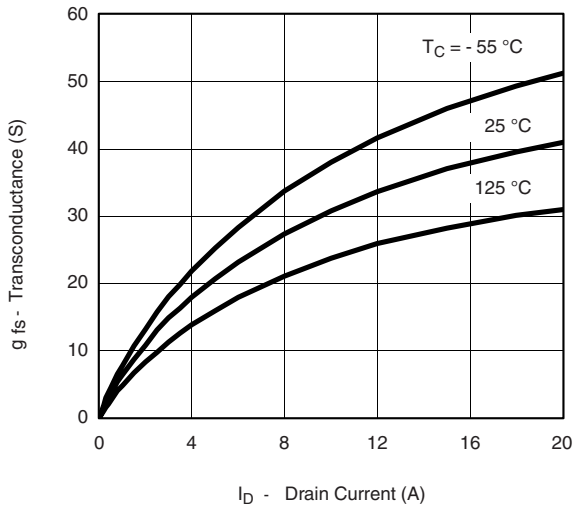
TYPICAL CHARACTERISTICS 25 °C unless noted



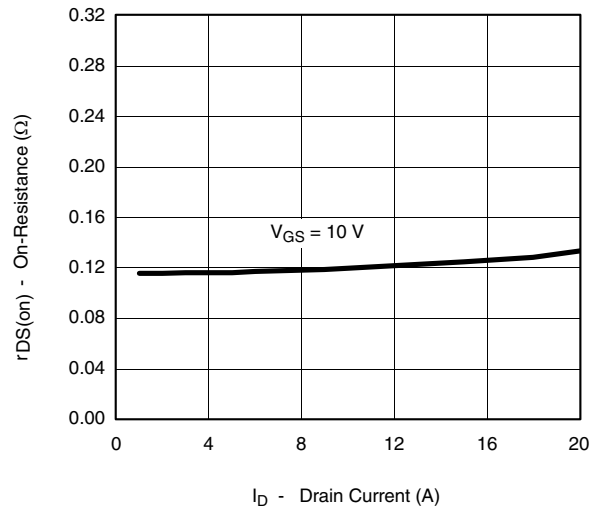
Output Characteristics



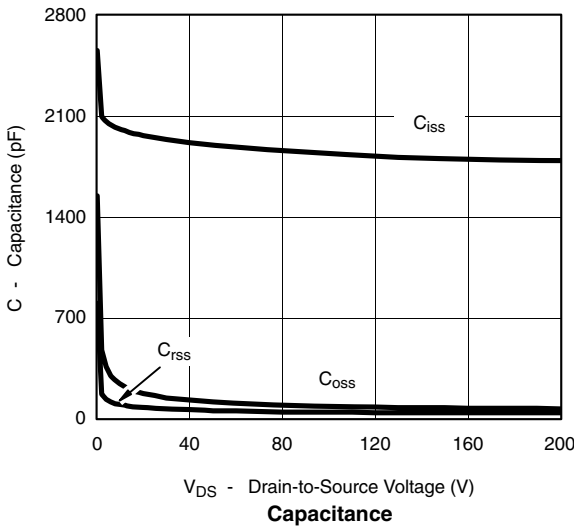
Transfer Characteristics



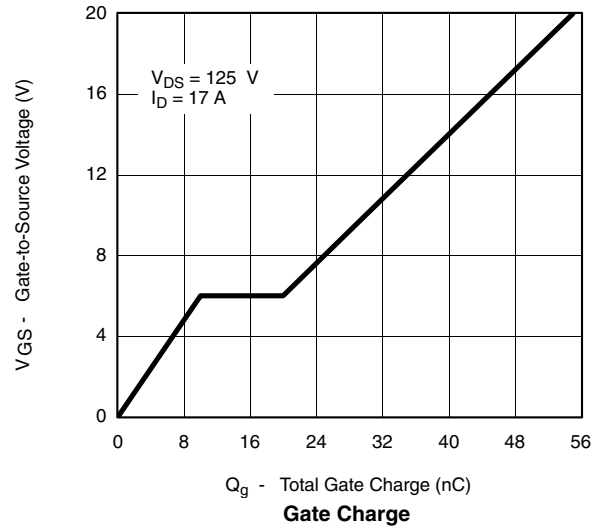
Transconductance



On-Resistance vs. Drain Current



Capacitance



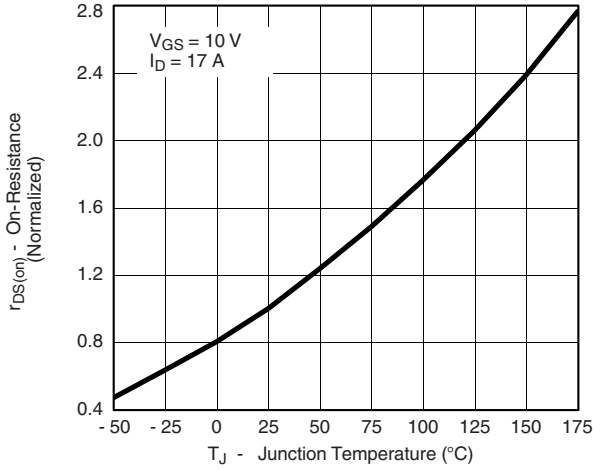
Gate Charge

SUD17N25-165

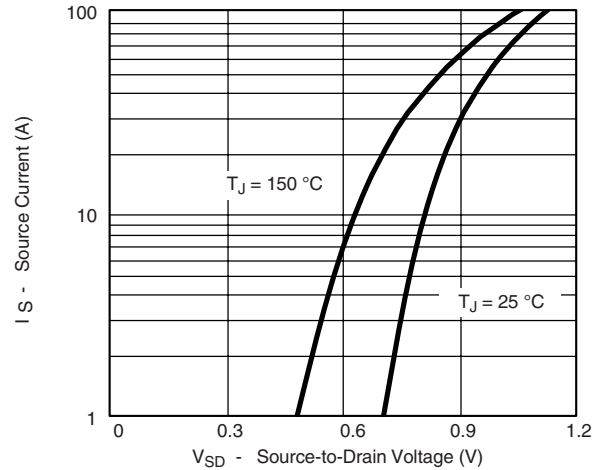


Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C unless noted

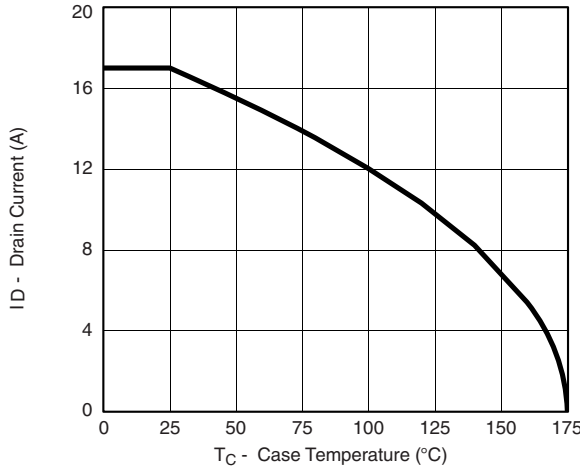


On-Resistance vs. Junction Temperature

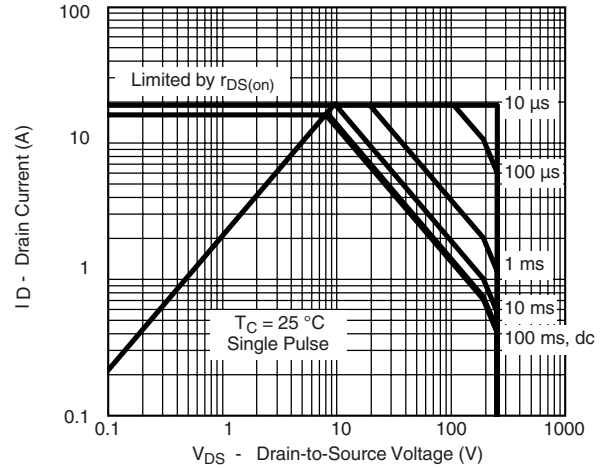


Source-Drain Diode Forward Voltage

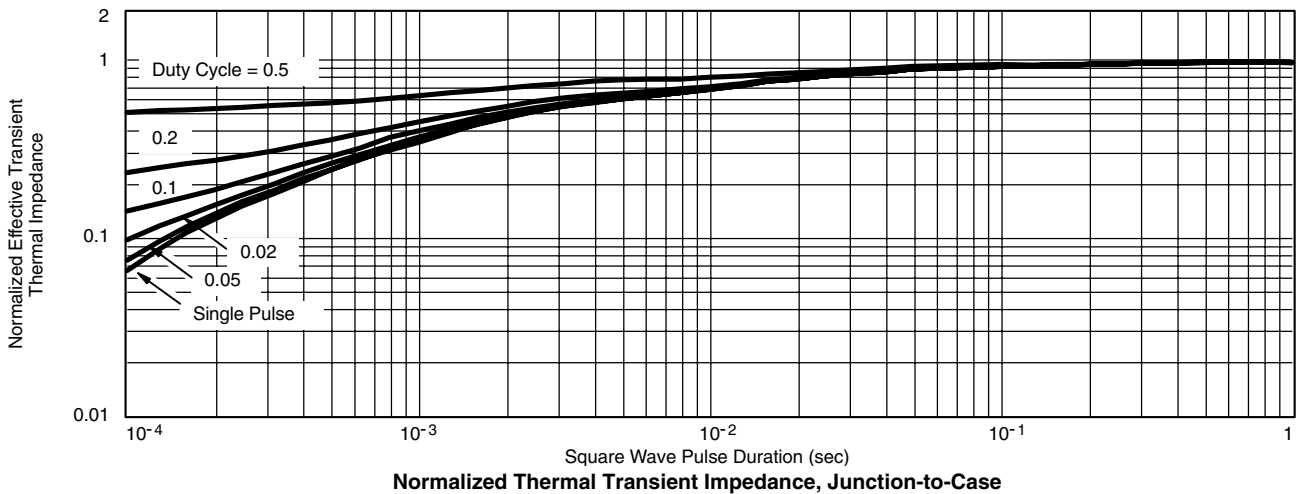
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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